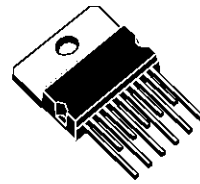


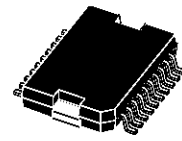
## 2.5A HIGH-SIDE DRIVER INDUSTRIAL INTELLIGENT POWER SWITCH

- 2.5A OUTPUT CURRENT
- 9.5V TO 35V SUPPLY VOLTAGE RANGE
- INTERNAL CURRENT LIMITING
- THERMAL SHUTDOWN
- OPEN GROUND PROTECTION
- INTERNAL NEGATIVE VOLTAGE CLAMPING TO  $V_S - 50V$  FOR FAST DEMAGNETIZATION
- DIFFERENTIAL INPUTS WITH LARGE COMMON MODE RANGE AND THRESHOLD HYSTERESIS
- UNDERVOLTAGE LOCKOUT WITH HYSTERESIS
- OPEN LOAD DETECTION
- TWO DIAGNOSTIC OUTPUTS
- OUTPUT STATUS LED DRIVER
- NON DISSIPATIVE SHORT CIRCUIT PROTECTION
- PROTECTION AGAINST AND SURGE TRANSIENT (IEC 801-5)
- IMMUNITY AGAINST BURST TRANSIENT (IEC 801-4)
- ESD PROTECTION (HUMAN BODY MODEL  $\pm 2KV$ )

### MULTIPOWER BCD TECHNOLOGY



MULTIWATT11 (in line)



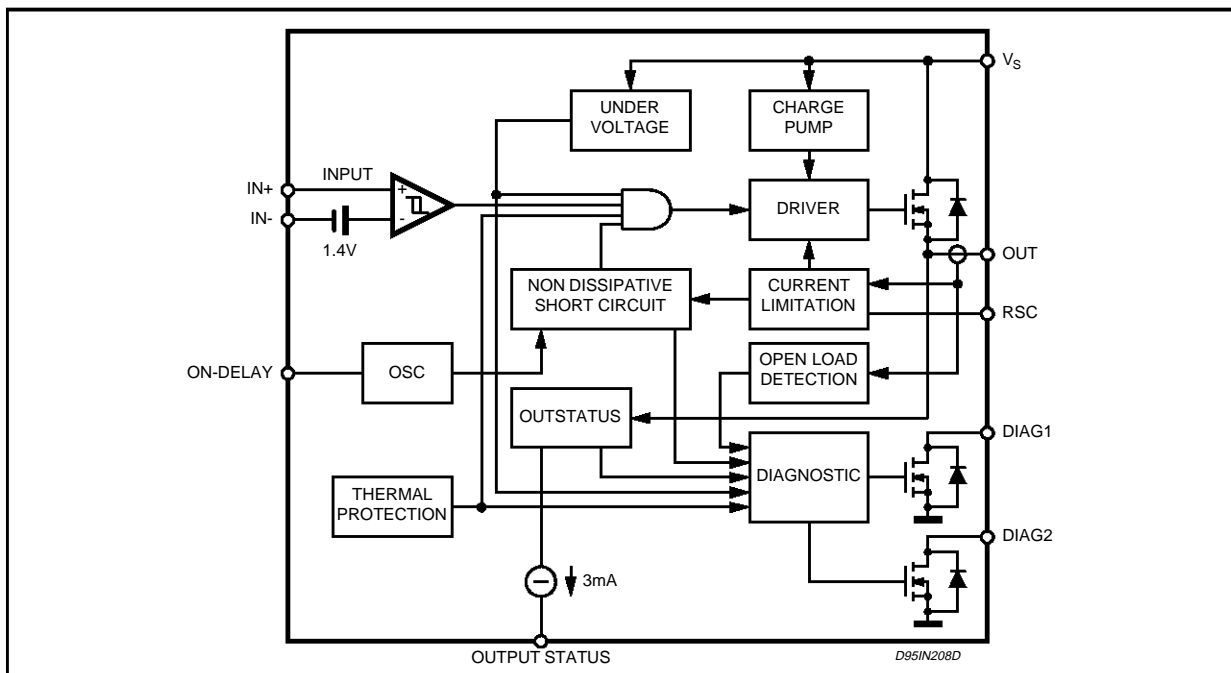
PowerSO20

ORDERING NUMBERS: L6370L (MULTIWATT11)  
L6370D (PowerSO20)

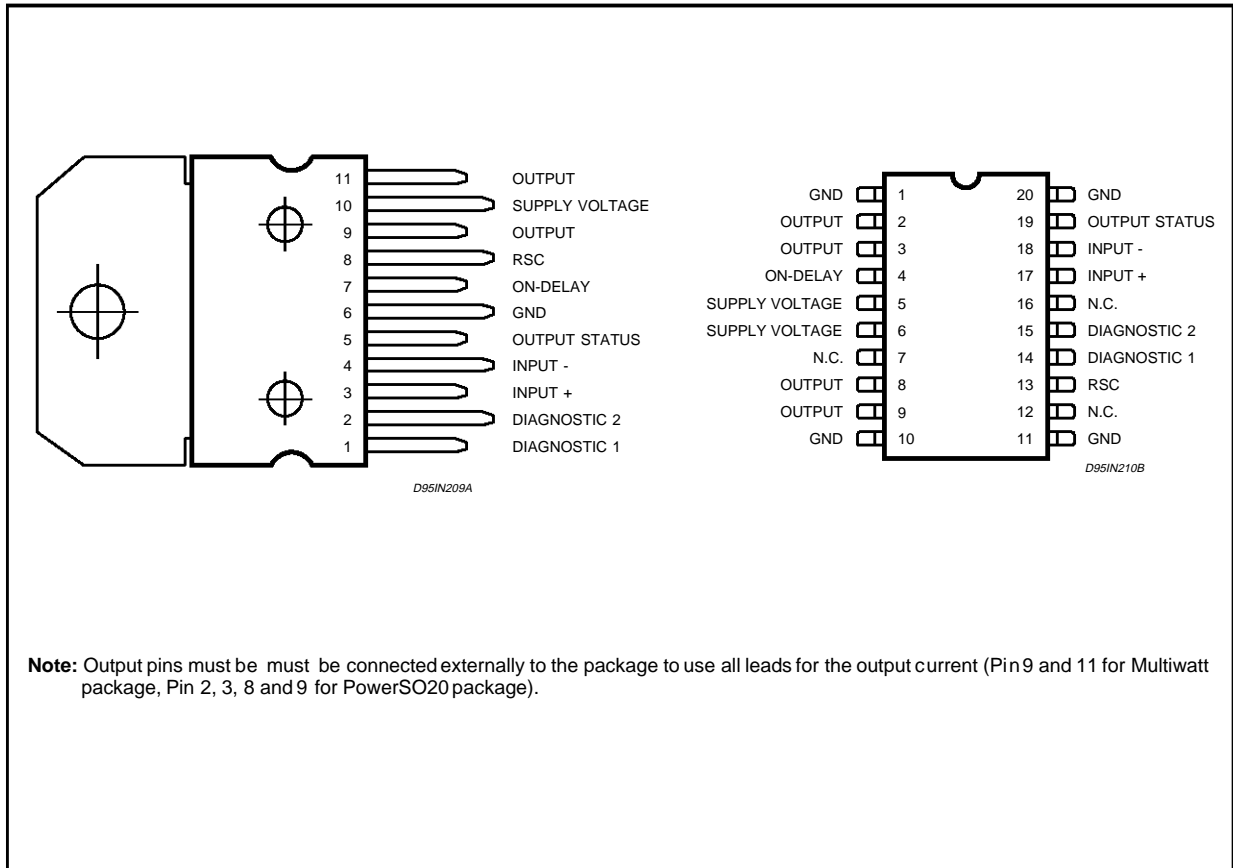
### DESCRIPTION

The L6370 is a monolithic Intelligent Power Switch in Multipower BCD Technology, for driving inductive or resistive loads. An internal Clamping Diode enables the fast demagnetization of inductive loads. Diagnostic for CPU feedback and extensive use of electrical protections make this device extremely rugged and specially suitable for industrial automation applications.

### BLOCK DIAGRAM



**PIN CONNECTION (Top view)**



**ABSOLUTE MAXIMUM RATINGS (Pin numbering referred to Multiwatt package)**

Symbol	Parameter	Value	Unit
$V_S$	Supply Voltage (Pin 10) ( $T_W < 10\text{ms}$ )	50	V
$V_S - V_O$	Supply to Output Differential Voltage. See also $V_{CI}$ (Pins 10 - 9)	internally limited	V
$V_{od}$	Externally Forced Voltage (Pin7)	-0.3 to 7	V
$I_{od}$	Externally Forced Current (Pin7)	$\pm 1$	mA
$V_i$	Input Voltage (Pins 3/4)	-10 to $V_S + 10$	V
$V_i$	Differential Input Voltage (Pins 3 - 4)	43	V
$I_i$	Input Current (Pins 3/4)	20	mA
$I_O$	Output Current (Pin 9). See also ISC (Pin 9)	internally limited	A
$P_{tot}$	Power Dissipation. See also THERMAL CHARACTERISTICS.	internally limited	W
$T_{op}$	Operating Temperature Range ( $T_{amb}$ )	-25 to +85	°C
$T_{stg}$	Storage Temperature	-55 to 150	°C
$E_i$	Energy Induct. Load $T_J = 85^\circ\text{C}$	1	J

**THERMAL DATA**

Symbol	Description	Multiwatt	PowerSO20	Unit
$R_{th\ j\text{-case}}$	Thermal Resistance Junction-case	Max. 1.5	1.5	°C/W
$R_{th\ j\text{-amb}}$	Thermal Resistance Junction-ambient	Max. 35	-	°C/W

**PIN FUNCTION** (pin numbering referred to Multiwatt package)

N.	Name	Function
1	DIAG1	DIAGNOSTIC 1 output. This open drain reports the IC working conditions. (See Diagnostic truth table)
2	DIAG1	DIAGNOSTIC 2 output. This open drain reports the IC working conditions. (See Diagnostic truth table)
3	IN -	Comparator non inverting input
4	IN+	Comparator inverting input
5	OUTSTATUS	This current source output is capable of driving a LED to signal the status of the output pin. The pin is active (source current) when the output pin is considered high (See fig 1)
6	GND	Ground
7	ON-DELAY	Programmable ON time interval duration during short circuit operation
8	RSC	Current limitation setting.
9	OUTPUT	High Side output with built-in current limitation
10	V <sub>S</sub>	Supply Voltage Input, the value of the supply voltage is monitored to detect under voltage condition
11	OUTPUT	High Side output with built-in current limitation

**ELECTRICAL CHARACTERISTICS** (V<sub>S</sub> = 24V; T<sub>J</sub> = -25 to +125°C, unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V <sub>smin</sub>	Supply Voltage for Valid Diagnostics	I <sub>diag</sub> > 0.5mA ; V <sub>dg1</sub> = 1.5V	4		35	V
V <sub>s</sub>	Supply Voltage (operative)		9.5	24	35	V
I <sub>q</sub>	Quiescent Current I <sub>out</sub> = I <sub>os</sub> = 0	V <sub>il</sub> V <sub>ih</sub>		0.8 3	1.4 5	mA mA
V <sub>sth1</sub>	Undervoltage Threshold 1	(See fig. 1), T <sub>amb</sub> = 0 to +85°C	8.5	9	9.5	V
V <sub>sth2</sub>	Undervoltage Threshold 2		8	8.5	9	V
V <sub>shys</sub>	Supply Voltage Hysteresis		300	500	700	mV
I <sub>sc</sub>	Short Circuit Current	V <sub>S</sub> = 9.5 to 35V; R <sub>L</sub> = 2Ω 5kΩ < R <sub>SC</sub> < 30kΩ	15/R <sub>SC</sub> (kΩ)			A
		0 < R <sub>SC</sub> < 5kΩ	2.6	3.2	4	A
V <sub>don</sub>	Output Voltage Drop	I <sub>out</sub> = 2.0A T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C I <sub>out</sub> = 2.5A T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C		200 320 250 400	280 440 350 550	mV mV mV mV
I <sub>oslk</sub>	Output Leakage Current	V <sub>i</sub> = V <sub>il</sub> ; V <sub>o</sub> = 0V			500	μA
V <sub>ol</sub>	Low State Out Voltage	V <sub>i</sub> = V <sub>il</sub> ; R <sub>L</sub> = ∞		0.8	1.5	V
V <sub>cl</sub>	Internal Voltage Clamp (V <sub>S</sub> - V <sub>O</sub> )	I <sub>o</sub> = 1A Single Pulsed: T <sub>p</sub> = 300μs	48	53	58	V
I <sub>old</sub>	Open Load Detection Current	V <sub>i</sub> = V <sub>ih</sub> ; T <sub>amb</sub> = 0 to +85°C	1	3	6	mA
V <sub>id</sub>	Common Mode Input Voltage Range (Operative)	V <sub>S</sub> = 18 to 35V	-7		15	V
I <sub>ip</sub>	Input Bias Current	V <sub>i</sub> = -7 to 15V; -I <sub>n</sub> = 0V	-250		250	μA
V <sub>ith</sub>	Input Threshold Voltage	V <sub>+In</sub> > V <sub>-In</sub>	0.8	1.4	2	V
V <sub>iths</sub>	Input Threshold Hysteresis Voltage	V <sub>+In</sub> > V <sub>-In</sub>	50		400	mV
R <sub>id</sub>	Diff. Input Resistance	0 < +I <sub>n</sub> < +16V; -I <sub>n</sub> = 0V -7 < +I <sub>n</sub> < 0V; -I <sub>n</sub> = 0V		400 150		KΩ KΩ
I <sub>lik</sub>	Input Offset Current	V <sub>+In</sub> = V <sub>-In</sub> +I <sub>i</sub>	-20		+20	μA
		0V < V <sub>i</sub> < 5.5V -I <sub>i</sub>	-75	-25		μA
		-I <sub>n</sub> = GND +I <sub>i</sub>		+10	+50	μA
		0V < V <sub>+In</sub> < 5.5V -I <sub>i</sub>	-250	-125		μA
		+I <sub>n</sub> = GND +I <sub>i</sub>	-100	-30		μA
		0V < V <sub>-In</sub> < 5.5V -I <sub>i</sub>	-50	-15		μA

**ELECTRICAL CHARACTERISTICS** (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{oth1}$	Output Status Threshold 1 Voltage	(See fig. 1)	4.5	5	5.5	V
$V_{oth2}$	Output Status Threshold 2 Voltage	(See fig. 1)	4	4.5	5.0	V
$V_{ohys}$	Output Status Threshold Hysteresis	(See fig. 1)	300	500	700	mV
$I_{osd}$	Output Status Source Current	$V_{out} > V_{oth1}$ ; $V_{os} = 2.5V$	2		4	mA
$V_{osd}$	Active Output Status Driver Drop Voltage	$V_s - V_{os}$ ; $I_{os} = 2mA$ $T_{amb} = 0$ to $+85^{\circ}C$		1.5	3	V
$I_{oslk}$	Output Status Driver Leakage Current	$V_{out} < V_{oth2}$ ; $V_{os} = 0V$ $V_s = 9.5$ to $35V$			25	$\mu A$
$V_{dgl}$	Diagnostic Drop Voltage	D1 / D2 = L; $I_{diag} = 0.5mA$ D1 / D2 = L; $I_{diag} = 3mA$		40 250		mV mV
$I_{dglk}$	Diagnostic Leakage Current	D1 / D2 = H; $0 < V_{dg} < V_s$ $V_s = 9.5$ to $35V$			5	$\mu A$

**SOURCE DRAIN NDMOS DIODE**

$V_{fsd}$	Forward On Voltage	@ $I_{fsd} = 2.5A$		1	1.5	V
$I_{fp}$	Forward Peak Current	$t = 10ms$ ; $d = 20\%$			6	A
$t_{rr}$	Reverse Recovery Time	$I_f = 2.5A$ di/dt = $25A/\mu s$		200		ns
$t_{fr}$	Forward Recovery Time			100		ns

**THERMAL CHARACTERISTICS**

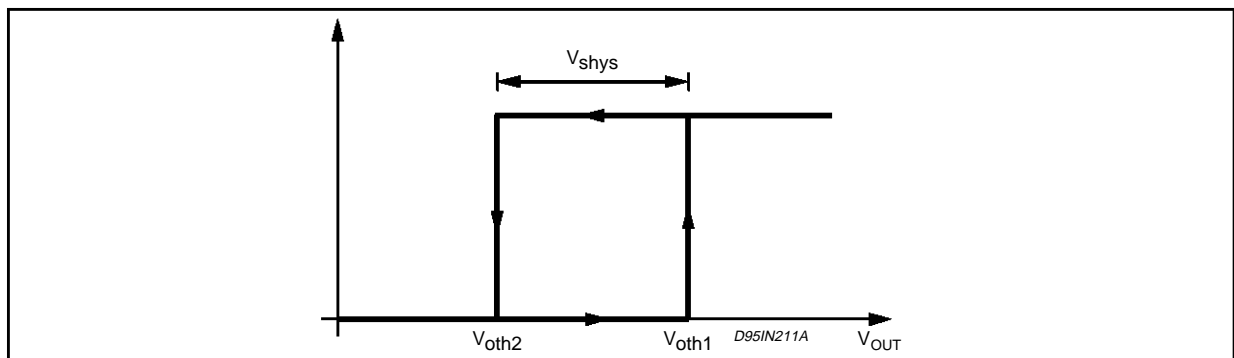
$\Theta_{Lim}$	Junction Temp. Protect.		135	150		$^{\circ}C$
$\Theta_{TH}$	Thermal Hysteresis			20		$^{\circ}C$

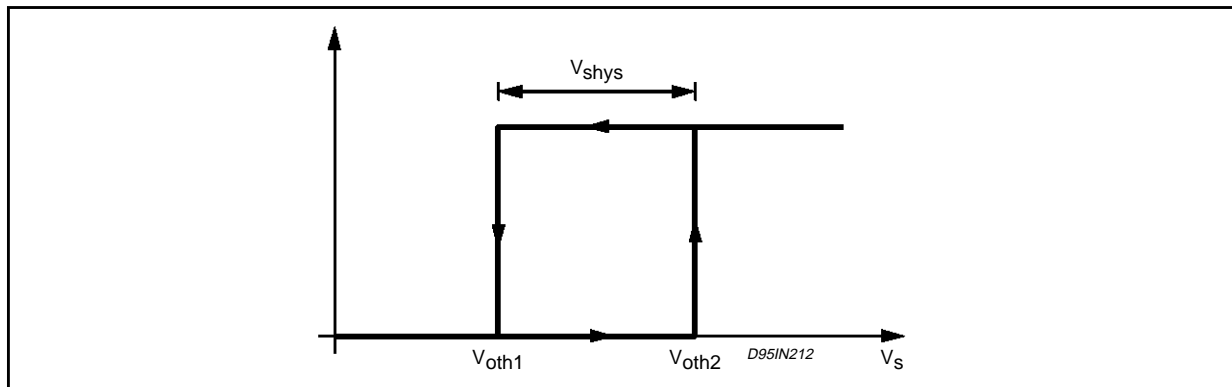
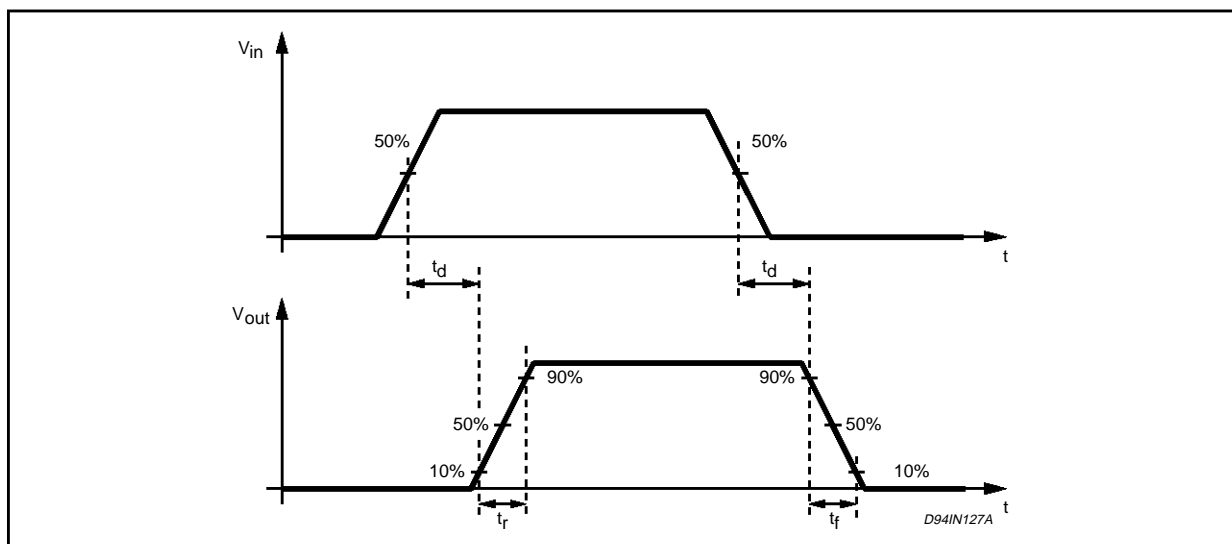
Note  $V_{il} \leq 0.8V$ ,  $V_{ih} \geq 2V$  @ ( $V+In > V-In$ )

**AC OPERATION** (pin numbering referred to Multiwatt package)

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_r - t_f$	9 vs 4	Rise or Fall Time	$V_s = 24V$ ; $R_l = 70\Omega$ ; $R_l$ to ground		20		$\mu s$
$t_d$	9 vs 3	Delay Time			5		$\mu s$
dV/dt	9, 11	Slew Rate (Rise and Fall Edge)		0.7	1	1.5	V/ $\mu s$
$t_{ON}$	7	On time during Short Circuit Condition	$50pF < C_{DON} < 2nF$		1.28		$\mu s/pF$
$t_{OFF}$		Of time during hort Circuit Condition			64		$t_{ON}$
$f_{max}$		Maximum Operating Frequency			25		KHz

**Figure 1: Output Status Hysteresis**



**Figure 2:** Undervoltage Comparator Hysteresis**Figure 3:** Switching Waveforms**DIAGNOSTIC TRUTH TABLE**

Diagnostic Conditions	Input	Output	Diag1	Diag2
Normal Operation	L H	L H	H H	H H
Open Load Condition ( $I_o < I_{old}$ )	L H	L H	H L	H H
Short to $V_S$	L H	H H	L L	H H
Short Circuit to Ground ( $I_o = I_{sc}$ ) (**) (pin ON-DELAY grounded)	H	H (*) L	H H	H H
Output DMOS Open	L H	L L	H L	H H
Overtemperature	L H	L L	H H	L L
Supply Undervoltage ( $V_S < V_{sth2}$ )	L H	L L	L L	L L

(\*) According to the intervention of the current limiting block.

(\*\*) A cold lamp filament, or a capacitive load may activate the current limiting circuit of the IPS, when the IPS is initially turned on.

## INPUT SECTION

The input section is an high impedance differential stage with high common and differential mode range. There's built-in offset of +1.4V (typical value) and an hysteresis of 400mV (maximum value), to ensure high noise immunity.

## DIAGNOSTIC LOGIC

The operating conditions of the device are permanently monitored and the following occurrences are signalled via the DIAG1/DIAG2 open-drain output pins:

- Short Circuit versus ground.  
A current limiting circuit fixes at  $I_{sc} = 3.2A$  (typical value) the maximum current that can be sourced from the OUTPUT pin (for more details see short circuit operation section).
- Short Circuit versus Vs.
- Under Voltage(UV)
- Over Temperature (OVT)
- Open Load, if the output current is less than 3mA (typical value).
- Output DMOS Open  
according to the diagnostic Truth Table:

## SHORT CIRCUIT OPERATION

in order to minimise the power dissipation when the output is shorted to grounded, an innovative, non dissipative short circuit protection (patent pending) is implemented, avoiding, thus the intervention of the thermal protection in most cases.

Whenever the output is shorted to ground, or, generally speaking, an over current is sinked by the load, the output devices is driven in linear mode, sourcing the  $I_{sc}$  current (typically 3.2A) for a time interval ( $t_{on}$ ) defined by means of the external  $C_{ON}$  capacitor connected between the ON-DELAY pin and GND. Whether the short circuit cease within the  $t_{on}$  interval the DIAG2 output status is not affected, acting as a Programmable Diagnostic Delay.

This function allow the device to drive a capacitive load or a filament lamp (that exhibits a very low resistance during the initial heading phase) without the intervention of the diagnostic.

If the short circuit lasts for the whole  $t_{on}$  interval, the output DMOS is switched OFF and the DIAG2 goes low, for a time interval  $t_{off}$  lasting 64 times  $t_{on}$ .

At the end of the  $t_{off}$  interval if the short circuit condition is still present, the output DMOS is turned ON (and the DIAG2 goes high - see fig4) for another  $t_{on}$  interval and the sequence starts again, or, whether not, the normal condition op-

eration is resumed.

The  $t_{on}$  interval can be set to lasts between 64 $\mu s$  and 2.56ms for a  $C_{ON}$  capacitor value ranging between 50pF and 2nF to have:

$$t_{on} (\mu s) = 1.28 C_{ON} (pF)$$

If the ON-DELAY pin is grounded the non dissipative short circuit protection is disabled, and the  $I_{sc}$  current is delivered until the Overtemperature Protection shuts the device off. The behaviour of the DIAG2 output is, in this situation, showed in the Diagnostic Truth Table.

## OVERTEMPERATURE PROTECTION (OVT)

If the chip temperature exceeds  $\Theta_{lim}$  (measured in a central position in the chip) the chip deactivates itself.

The following actions are taken:

all the output stage is switched off;

the signal DIAG2 is activated (active low).

Normal operation is resumed as soon as (typically after some seconds) the chip temperature monitored goes back below  $\Theta_{lim} - \Theta_H$ .

The different thresholds with hysteretic behavior assure that no intermittent conditions can be generated.

## UNDERVOLTAGE PROTECTION (UV)

The supply voltage is expected to range from 9.5V to 35V, even if its reference value is considered to be 24V.

In this range the device operates correctly.

Below 9.5V the overall system has to be considered not reliable.

Protection will thus shut off the output whenever the supply voltage falls below the mask fixed by the  $V_{sth1}$  (9V typ.) and  $V_{sth2}$  (8.5V typ.).

The hysteresis (see fig. 2) ensures a non intermittent behavior at low supply voltage with a superimposed ripple.

The Under Voltage status is signalled via the DIAG1 and DIAG2 outputs (see the Diagnostic Truth Table).

## DEMAGNETIZATION OF INDUCTIVE LOADS

An internal zener diode, limiting the voltage across the Power MOS to between 50 and 60V ( $V_{cl}$ ), provides safe and fast demagnetization of inductive loads without external clamping devices.

The maximum energy that can be absorbed from an inductive load is specified as 1J (at  $T_j = 85^\circ C$ ) (see figure 2)

Figure 4: L6370 Short Circuit Operation Waveforms

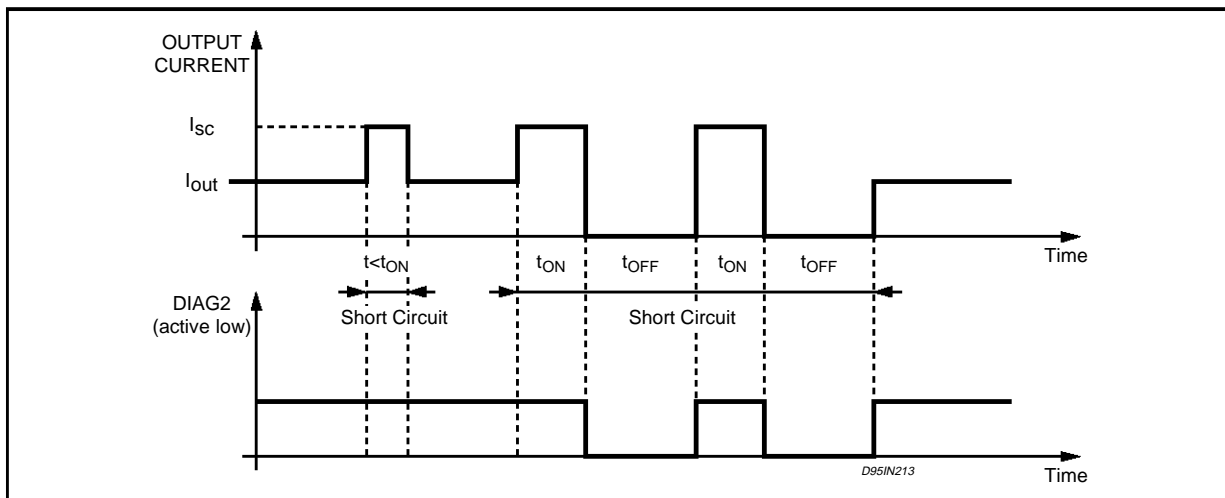
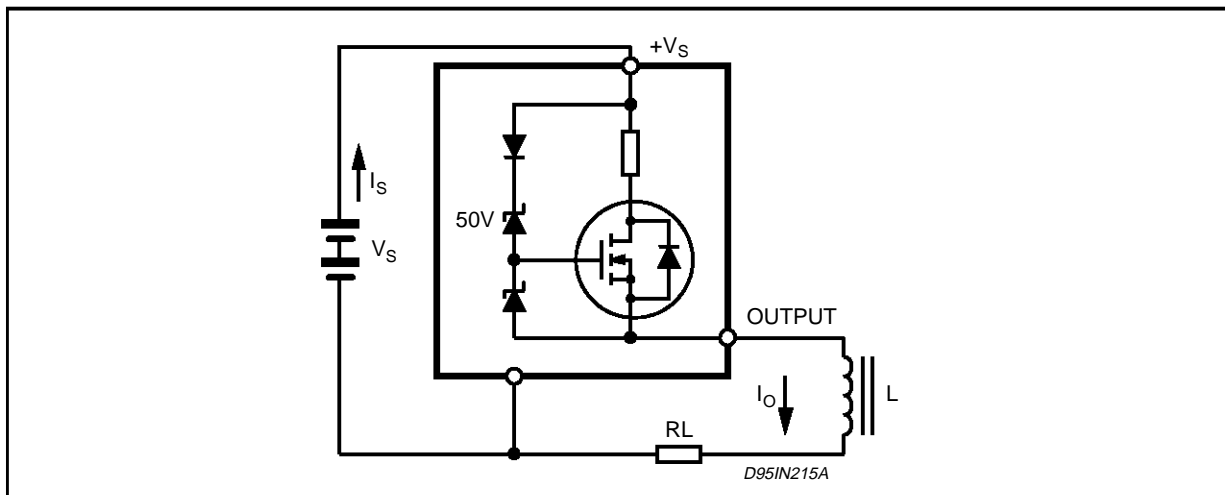
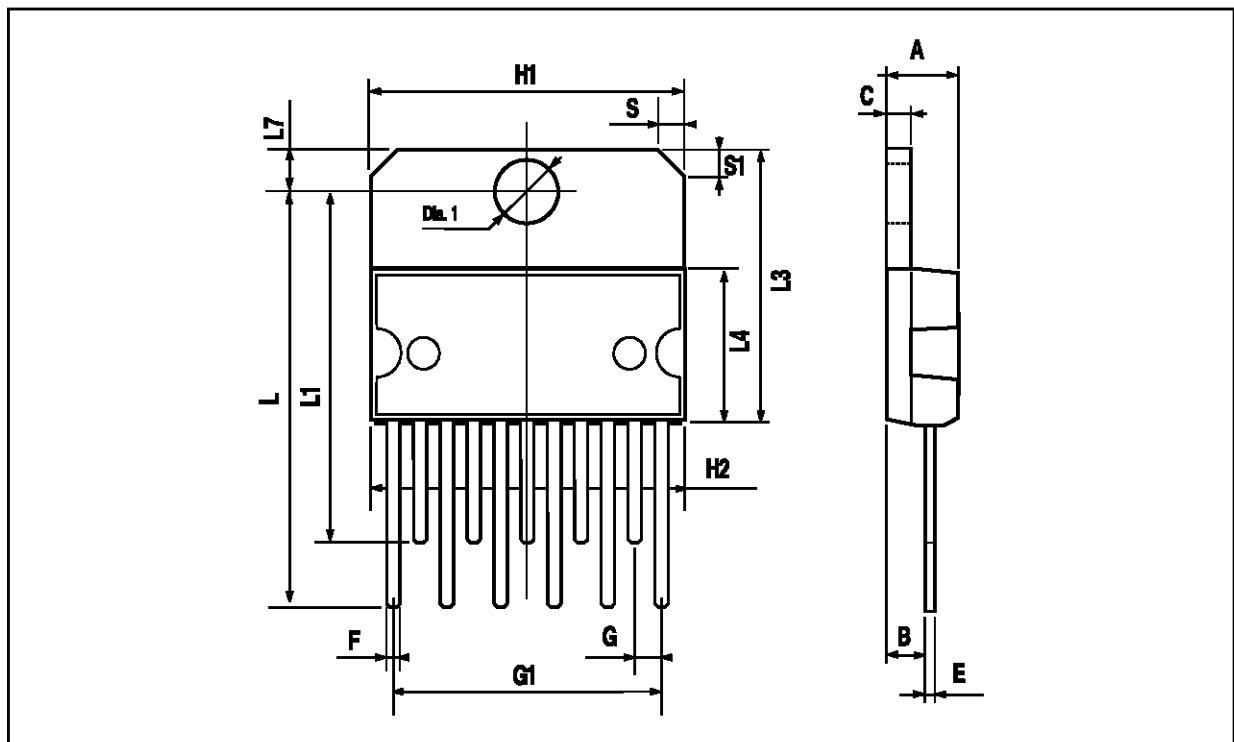


Figure 5: Inductive Load Equivalent Circuit



MULTIWATT11 (in line) PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			5			0.197
B			2.65			0.104
C			1.6			0.063
E	0.49		0.55	0.019		0.022
F	0.88		0.95	0.035		0.037
G	1.57	1.7	1.83	0.062	0.067	0.072
G1	16.87	17	17.13	0.664	0.669	0.674
H1	19.6			0.772		
H2			20.2			0.795
L	26.4		26.9	1.039		1.059
L1	22.35		22.85	0.880		0.900
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152

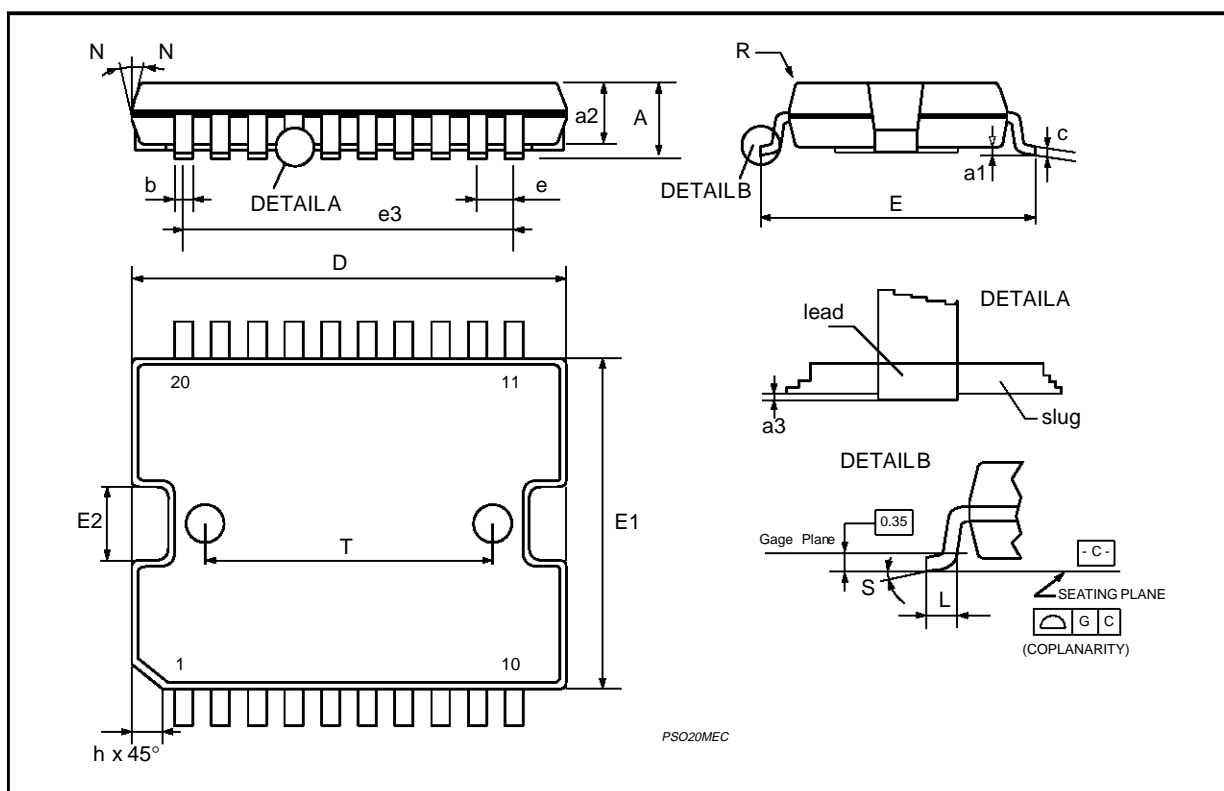




## PowerSO20 PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			3.60			0.1417
a1	0.10		0.30	0.0039		0.0118
a2			3.30			0.1299
a3	0		0.10	0		0.0039
b	0.40		0.53	0.0157		0.0209
c	0.23		0.32	0.009		0.0126
D (1)	15.80		16.00	0.6220		0.6299
E	13.90		14.50	0.5472		0.570
e		1.27			0.050	
e3		11.43			0.450	
E1 (1)	10.90		11.10	0.4291		0.437
E2			2.90			0.1141
G	0		0.10	0		0.0039
h			1.10			
L	0.80		1.10	0.0314		0.0433
N	10° (max.)					
S	8° (max.)					
T		10.0			0.3937	

(1) "D and E1" do not include mold flash or protrusions  
 - Mold flash or protrusions shall not exceed 0.15mm (0.006")



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